





N-CHANNEL ENHANCEMENT MODE MOSFET

Features

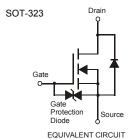
- Low On-Resistance: R_{DS(ON)}
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected up to 2KV
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

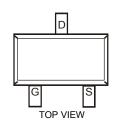
Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)









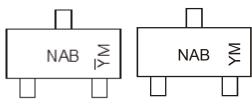
Ordering Information (Note 4)

| Part Number | Case | Packaging |
|-------------|---------|------------------|
| DMN2004WK-7 | SOT-323 | 3000/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



Chengdu A/T Site Shanghai A/T Site

NAB = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)

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\begin{align*}
\text{YM} = Date Code Marking for SAT (Chengdu Assembly/ Test site)
\end{align*}

Y or \overline{Y} = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Date Code Key

| Date Code Ney | | | | | | | | | | | | |
|---------------|-----|-----|------|-----|------|-----|-----|------|-----|------|-----|------|
| Year | 200 | 9 | 2010 | | 2011 | 20 | 12 | 2013 | | 2014 | 2 | 2015 |
| Code | W | | Х | | Υ | | Z | Α | | В | | С |
| | | | | | | - | | 1 | | 1 | | |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D |



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Cha | racteristic | | Symbol | Value | Units |
|-------------------------------|-----------------|--|-----------------|------------|-------|
| Drain-Source Voltage | | | V_{DSS} | 20 | V |
| Gate-Source Voltage | | | V_{GSS} | ±8 | V |
| Drain Current (Note 5) | Steady State | T _A = +25°C T _A = +85°C | I _D | 540 390 | mA |
| Pulsed Drain Current (Note 6) | | | I _{DM} | 1.5 | Α |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Units |
|---|----------------------------------|-------------|-------|
| Total Power Dissipation (Note 5) | P_{D} | 200 | mW |
| Thermal Resistance, Junction to Ambient | $R_{	hetaJA}$ | 625 | °C/W |
| Operating and Storage Temperature Range | T _{J,} T _{STG} | -55 to +150 | °C |

Notes: 5. Device mounted on FR-4 PCB.

6. Pulse width ${\le}10\mu S,$ Duty Cycle ${\le}1\%.$

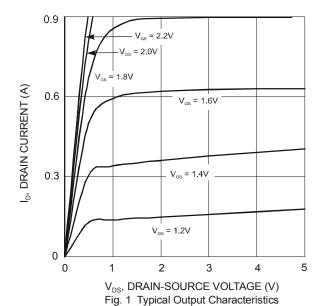
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

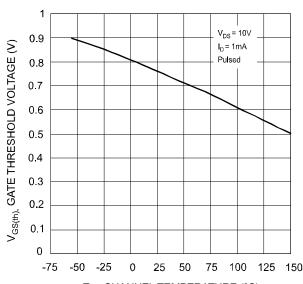
| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition | |
|--|----------------------|-----|-----|------|------|--|--|
| Characteristic Symbol Min Typ Max Unit Test Condition OFF CHARACTERISTICS (Note 7) | | | | | | | |
| ` ' | D) / | 20 | 1 | | | V 0V 1 40 A | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 20 | _ | | V | $V_{GS} = 0V, I_D = 10\mu A$ | |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | _ | 1 | μΑ | $V_{DS} = 16V, V_{GS} = 0V$ | |
| Gate-Source Leakage | I _{GSS} | _ | _ | ±1 | μA | $V_{GS} = \pm 4.5V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 7) | | | | | | · | |
| Gate Threshold Voltage | V _{GS(th)} | 0.5 | _ | 1.0 | V | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | |
| | | | 0.4 | 0.55 | | $V_{GS} = 4.5V, I_D = 540mA$ | |
| Static Drain-Source On-Resistance | R _{DS (ON)} | _ | 0.5 | 0.70 | Ω | $V_{GS} = 2.5V, I_D = 500mA$ | |
| | | | 0.7 | 0.9 | | V _{GS} = 1.8V, I _D = 350mA | |
| Forward Transfer Admittance | Y _{fs} | 200 | _ | | ms | V _{DS} =10V, I _D = 0.2A | |
| Diode Forward Voltage (Note 7) | V_{SD} | 0.5 | _ | 1.4 | V | $V_{GS} = 0V, I_{S} = 115mA$ | |
| DYNAMIC CHARACTERISTICS(Note 8) | | | | | | | |
| Input Capacitance | C _{iss} | _ | _ | 150 | pF | 101/11/001/ | |
| Output Capacitance | Coss | | | 25 | pF | $V_{DS} = 16V, V_{GS} = 0V$ f = 1.0MHz | |
| Reverse Transfer Capacitance | C _{rss} | | | 20 | pF | 1 - 1.0101112 | |

Notes: 7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to production testing.







T_{ch}, CHANNEL TEMPERATURE (°C)
Fig. 3 Gate Threshold Voltage vs. Channel Temperature

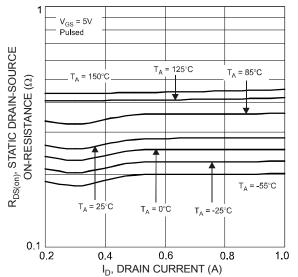


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

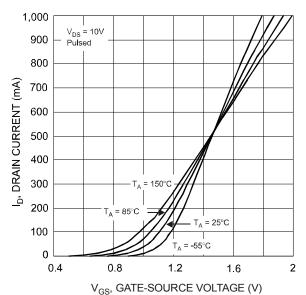


Fig. 2 Reverse Drain Current vs. Source-Drain Voltage

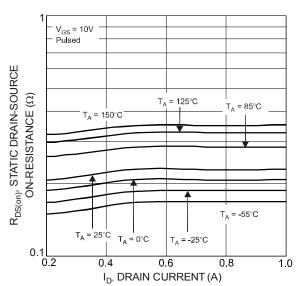


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

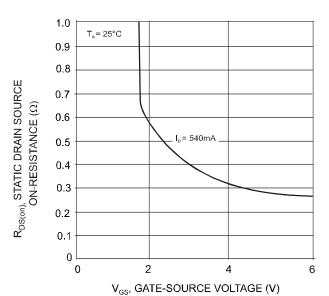


Fig. 6 Static Drain-Source, On-Resistance vs. Gate-Source Voltage



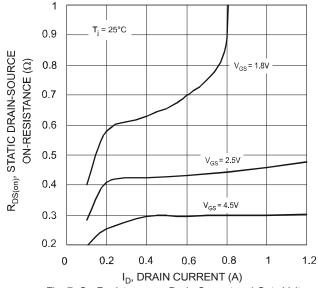
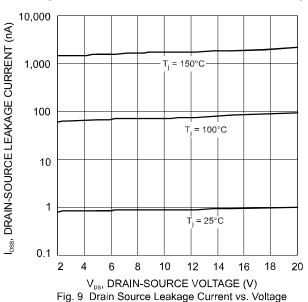


Fig. 7 On-Resistance vs. Drain Current and Gate Voltage



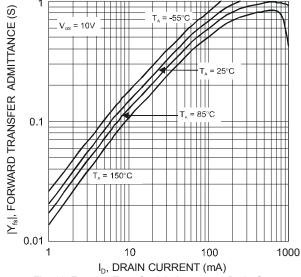


Fig. 11 Forward Transfer Admittance vs. Drain Current

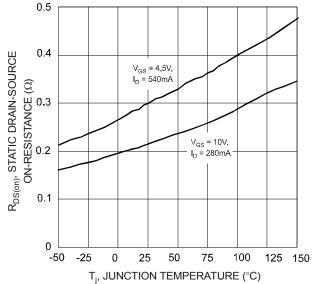


Fig. 8 Static Drain-Source, On-Resistance vs. Temperature

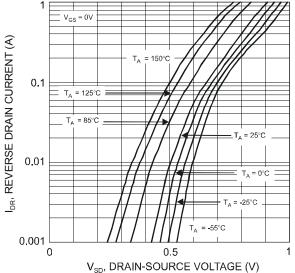
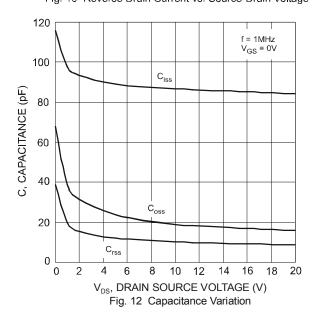


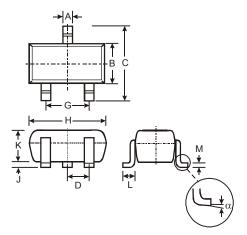
Fig. 10 Reverse Drain Current vs. Source-Drain Voltage





Package Outline Dimensions

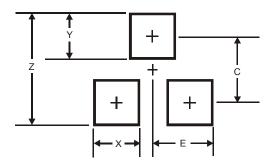
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



| SOT-323 | | | | | | | |
|----------------------|------|------|------|--|--|--|--|
| Dim | Min | Max | Тур | | | | |
| Α | 0.25 | 0.40 | 0.30 | | | | |
| В | 1.15 | 1.35 | 1.30 | | | | |
| С | 2.00 | 2.20 | 2.10 | | | | |
| D | - | - | 0.65 | | | | |
| G | 1.20 | 1.40 | 1.30 | | | | |
| Н | 1.80 | 2.20 | 2.15 | | | | |
| J | 0.0 | 0.10 | 0.05 | | | | |
| K | 0.90 | 1.00 | 0.95 | | | | |
| L | 0.25 | 0.40 | 0.30 | | | | |
| M | 0.10 | 0.18 | 0.11 | | | | |
| α | 0° | 8° | - | | | | |
| All Dimensions in mm | | | | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 2.8 |
| Х | 0.7 |
| Y | 0.9 |
| С | 1.9 |
| E | 1.0 |



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